# 2SA2153

# Bipolar Transistor –50V, –2A, Low VCE(sat), PNP Single



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#### **Features**

- Adoption of MBIT Process
- Low Saturation Voltage
- Large Current Capacity and Wide ASO

# **Typical Applications**

- Voltage Regulators
- Relay Drivers
- Lamp Drivers
- Electrical Equipment

### **SPECIFICATIONS**

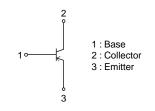
ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit	
Collector to Base Voltage	VCBO	-50	V	
Collector to Emitter Voltage	VCEO	-50	<b>V</b>	
Emitter to Base Voltage	VEBO	-6	V	
Collector Current	IC	-2	Α	
Collector Current (Pulse)	ICP	-4	Α	
Base Current	lΒ	-400	mA	
Collector Dissipation	(Note 2)	Do	1.3	W
	Tc=25°C	PC	3.5	W
Junction Temperature	Tj	150	°C	
Storage Temperature	Tstg	-55 to +150	°C	

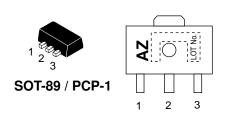
Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2 : Surface mounted on ceramic substrate(450mm<sup>2</sup> × 0.8mm)

#### **ELECTRICAL CONNECTION**



#### **MARKING**



## **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

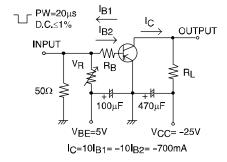
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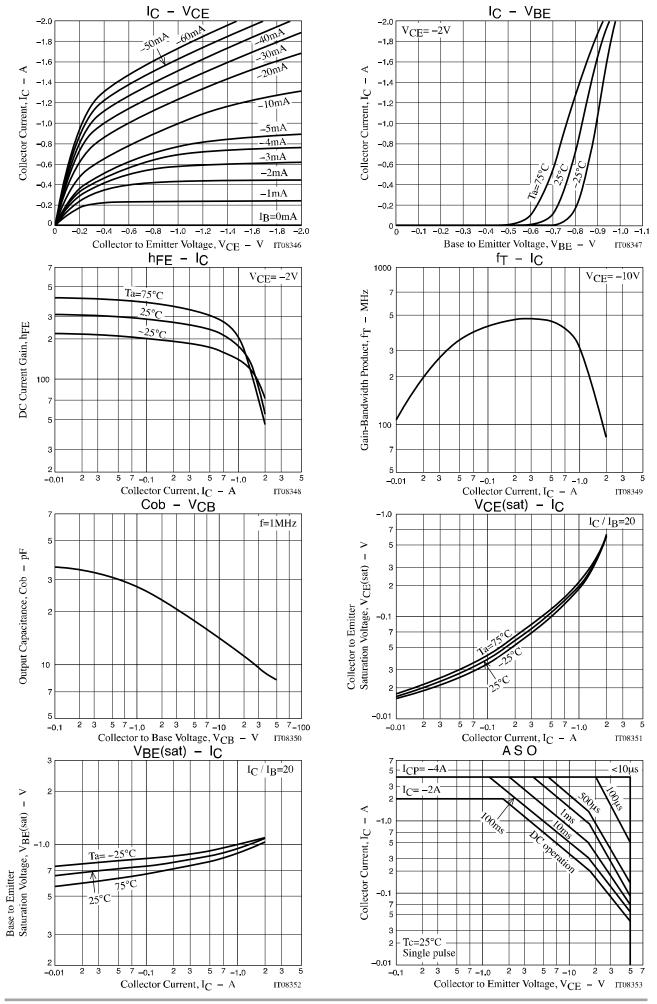
# **ELECTRICAL CHARACTERISTICS** at $Ta = 25^{\circ}C$ (Note 3)

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Parameter	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =-40V, I <sub>E</sub> =0A			-1	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =-4V, I <sub>C</sub> =0A			-1	μΑ
DC Current Gain	hFE1	V <sub>CE</sub> =-2V, I <sub>C</sub> =-100mA	200		560	
	hFE2	V <sub>CE</sub> =-2V,I <sub>C</sub> =-1.5A	40			
Gain-Bandwidth Product	fŢ	V <sub>CE</sub> =-10V, I <sub>C</sub> =-300mA		420		MHz
Output Capacitance	Cob	V <sub>CB</sub> =-10V, f=1MHz		16		pF
Collector to Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =-1A, I <sub>B</sub> =-50mA		-0.2	-0.4	V
Base to Emitter Saturation Voltage	V <sub>BE</sub> (sat)	IC=-1A, IB=-50mA		-0.9	-1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =-10μΑ, I <sub>E</sub> =0Α	-50			٧
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC=−1mA, RBE=∞	-50			٧
Emitter to Base Breakdown Voltage	V(BR)EBO	IE=-10μΑ, IC=0A	-6			٧
Turn-On Time	ton			35		ns
Storage Time	t <sub>stg</sub>	See specified Test  Circuit		200		ns
Fall Time	tf	Circuit		24		ns

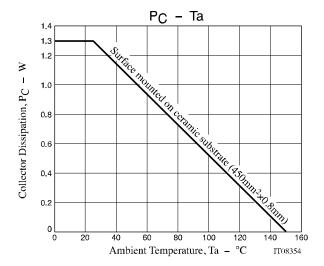
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

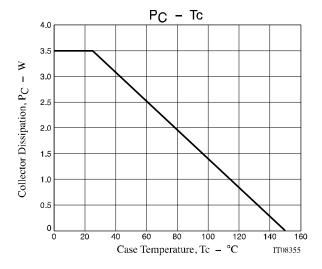
# **Switching Time Test Circuit**





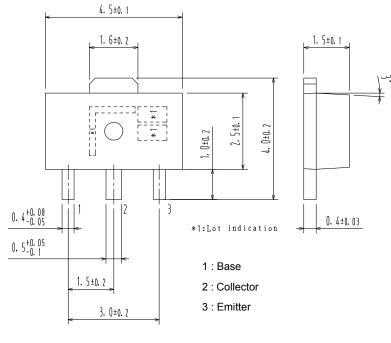
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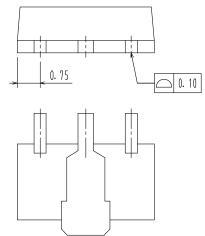




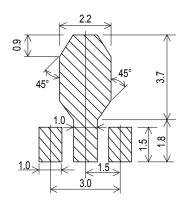
#### PACKAGE DIMENSIONS

unit : mm SOT-89 / PCP-1 CASE 419AU ISSUE O





# Recommended Soldering Footprint



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)	
2SA2153-TD-E AZ		SOT-89 / PCP-1 (Pb-Free)	1,000 / Tape & Reel	

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

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